

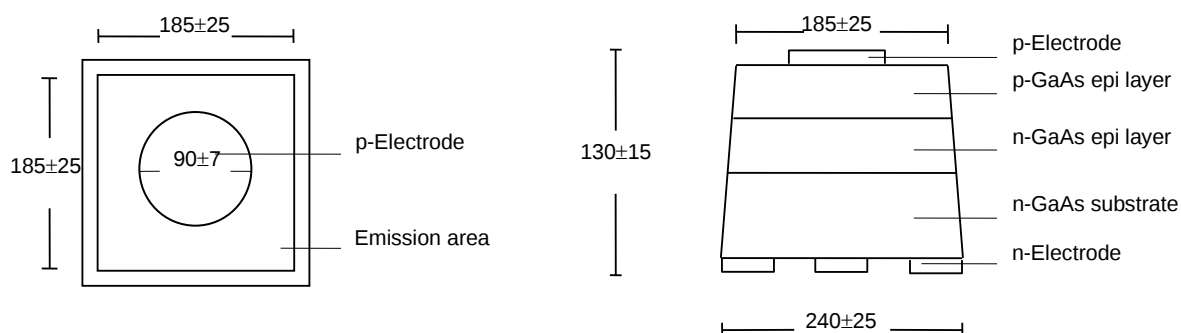
■ Features :

- GaAs/GaAs Wafer
- Good Spectral Matched to Si Detector

■ Typical Applications :

- Peripheral Device
- Photo Coupler
- Photo Interrupter

Outline Dimensions : (Unit: μm)



■ Physical Structure :

Chip dimension	Chip size	240 μm x 240 μm
	Thickness	130 μm
	Emission area	185 μm
	Bonding pad	90 μm
Electrode	Top: P (anode)	Gold
	Backside: N (cathode)	Gold alloy
Surface condition	Smooth	

■ Electro-Optical Characteristics : ($T_a = 25^\circ\text{C}$)

Parameter	Symbol	Condition	Min.	Typ.	Max.	Unit
Forward Voltage	V_F	$I_F = 20 \text{ mA}$	-	1.27	1.32	V
		$I_F = 100 \text{ mA}$	-	1.55	1.70	
Reverse Voltage	I_R	$V_R = 10 \text{ V}$	-	-	1.5	μA
Wavelength	λ_P	$I_F = 20 \text{ mA}$	920	940	960	nm
Spectral width at half height	$\Delta\lambda$	$I_F = 20 \text{ mA}$	-	50	-	nm
Radiant Power	P_o	$I_F = 20 \text{ mA}$	0.52	0.63	0.78	mW

■ Typical Electro-Optical Characteristics Curve:

Fig 1. Forward Current vs. Forward Voltage

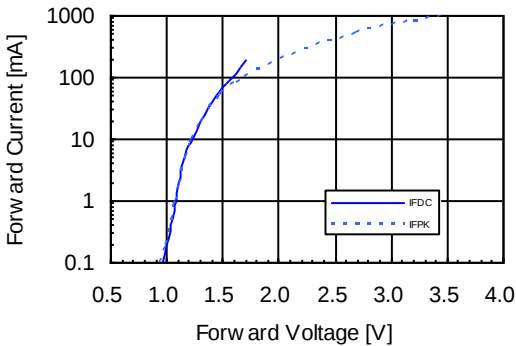


Fig 2. Relative Radiant Power vs. Wavelength

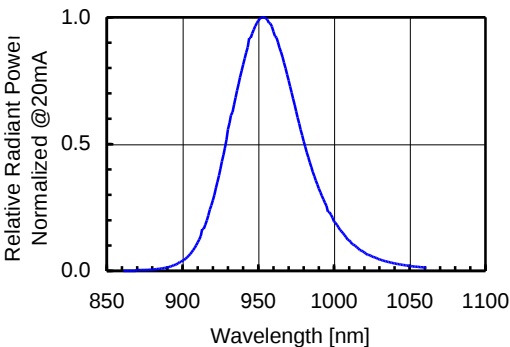


Fig 3. Relative Radiant Power
vs. Forward DC Current

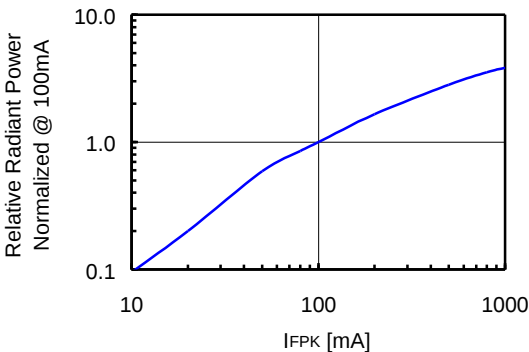


Fig 4. Relative Radiant Power
vs. Forward Peak Current

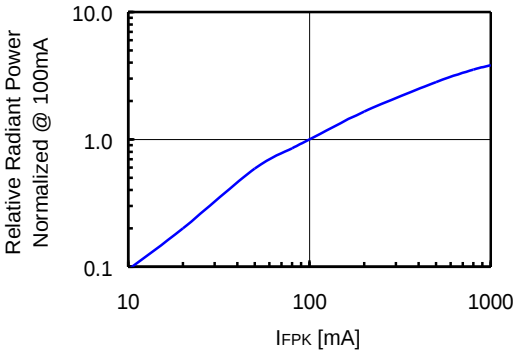


Fig 5. Forward DC Voltage vs. Temperature

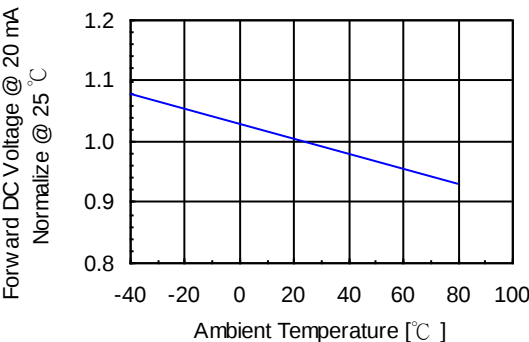


Fig 6. Relative Radiant Power vs. Temperature

